

Field Programmable Crystal Oscillator

Series CPPFX

- Programmed in the field with the PG-3200 oscillator programming instrument within seconds.
- Factory Programmable
- Can be programmed twice
- Standard Package Options
- Also available in 2.7V

Instrument Part Number:

CPPFXC1LZ-A5B6-XX.XXXX TS

| CPPFX | C | 1 | L | Z | A5 | B6 | XX.XXXX | TS |
|--------|---------------------|---|------------------------------------|---|--|--|------------------|-----------------------------------|
| SERIES | OUTPUT | PACKAGE STYLE | VOLTAGE | ADDED FEATURE | OPERATING TEMP | STABILITY | FREQUENCY | TRI-STATE |
| CPPFX | C = CMOS T = TTL | 1 = Full Size 4 = Half Size 5 = 3.2x5 Ceramic 7 = 5x7 Ceramic 8 = PLASTIC SMD | Blank = 5V L = 3.3V R = 2.7V | Blank = Cut Tape B = Bulk T = Tube Z = Tape and Reel | Blank = 0°C~+70°C A3 = -55~+125°C A5 = -20°C~+70°C A7 = -40°C~+85°C | B6 = ±100PPM BP = ±50PPM BR = ±25PPM | 0.50 ~ 133.00MHz | TS = Tri-State PD = Power Down |

Specifications:

| Description | Min | Typ | Max | Unit |
|---|--------------------|-----|--------------------|----------|
| Frequency Range: Programmable to any discrete frequency | 0.500 | | 133 | MHz |
| Available Stability Options: | -100 -50 -25 | | +100 +50 +25 | PPM |
| Programmable Supply Voltage: | | | | |
| (1-133 MHz) | 4.5 | 5.0 | 5.5 | V |
| (1-100 MHz) | 3.0 | 3.3 | 3.6 | V |
| (1-66.0 MHz) | 2.5 | 2.7 | 3.0 | V |
| Operating Temperature Range Options: | | | | |
| | -55 | | +125 | °C |
| | -20 | | +70 | °C |
| | -40 | | +85 | °C |
| Storage Temperature: | -55 | | +125 | °C |
| Aging: Ta=°25C,Vdd=5V/3.3V | | | ±5 | PPM/Year |

Programmable Output Level:

CMOS/TTL

Operating Conditions:

| Description | Min | Max | Unit |
|--|-----|-----|------|
| V_{DD} Supply Voltage | 2.7 | 5.5 | V |
| C_{TTL} Max capacitive load on outputs for TTL levels | | | |
| 4.5V-5.5V V _{DD} , ≤ 40 MHz | | 50 | pF |
| 4.5V-5.5V V _{DD} , 40 - 133 MHz | | 25 | pF |
| C_{CMOS} Max capacitive load on outputs for CMOS levels | | | |
| 4.5V-5.5V V _{DD} , ≤ 66 MHz | | 50 | pF |
| 4.5V-5.5V V _{DD} , 66 - 133 MHz | | 25 | pF |
| 3.0V-3.6V V _{DD} , ≤ 40 MHz | | 30 | pF |
| 3.0V-3.6V V _{DD} , 40 - 100 MHz | | 15 | pF |
| 2.5-3.0V V _{DD} , ≤ 66 MHz | | 25 | pF |



Output Clock Switching Characteristics:

| Description | Test Conditions | Min | Typ | Max | Unit |
|---|---|-----|-----|------|------|
| Duty Cycle: TTL @ 1.4V 4.5-5.5 V _{DD} | ≤ 50 MHz, C _L = 50 pF | 45 | - | 55 | % |
| | 50 - 66 MHz, C _L = 15 pF | 45 | - | 55 | % |
| | 66 - 125 MHz, C _L = 25 pF | 40 | - | 60 | % |
| | 125 - 133 MHz, C _L = 15 pF | 40 | - | 60 | % |
| Duty Cycle: CMOS @ V _{DD} /2 4.5-5.5 V _{DD} 3.0-3.6 V _{DD} | ≤ 66 MHz, C _L ≤ 25 pF | 45 | - | 55 | % |
| | 66 - 125 MHz, C _L ≤ 25 pF | 40 | - | 60 | % |
| | 125 - 133 MHz, C _L ≤ 15 pF | 60 | - | 60 | % |
| | ≤ 40 MHz, C _L ≤ 30 pF | 45 | - | 55 | % |
| Rise/Fall: | 0.8V - 2.0V, 4.5 - 5.5 V _{DD} , C _L = 50 pF | | | 1.8 | ns |
| | 0.8V - 2.0V, 4.5 - 5.5 V _{DD} , C _L = 25 pF | | | 1.2 | ns |
| | 0.8V - 2.0V, 4.5 - 5.5 V _{DD} , C _L = 15 pF | | | 0.9 | ns |
| | 0.2V - 0.8 * V _{DD} , 4.5 - 5.5 V _{DD} , C _L = 50 pF | | | 3.4 | ns |
| | 0.2V - 0.8 * V _{DD} , 3.0 - 3.6 V _{DD} , C _L = 30 pF | | | 4.0 | ns |
| | 0.2V - 0.8 * V _{DD} , 3.0 - 3.6 V _{DD} , C _L = 15 pF | | | 2.4 | ns |
| Start Up Time | From Power On | - | - | 2 | ms |
| Power Down Delay Time Synchronous Asynchronous | PWR_DOWN pin LOW to output Hi-Z, T = Frequency Oscillator Period | | T/2 | T+10 | ns |
| | | | 10 | 15 | ns |
| Output Disable Time Synchronous Asynchronous | OE pin LOW to output Hi-Z, T = Frequency Oscillator Period | | T/2 | T+10 | ns |
| | | | 10 | 15 | ns |
| Output Enable Time | | | | 100 | ns |
| RMS Period Jitter | ≤ 33.000 MHz | | 11 | 13 | ps |
| | > 33.000 MHz | | 8 | 11 | ps |
| Peak to Peak* | ≤ 33.000 MHz | | 80 | 110 | ps |
| | > 33.000 MHz | | 65 | 80 | ps |

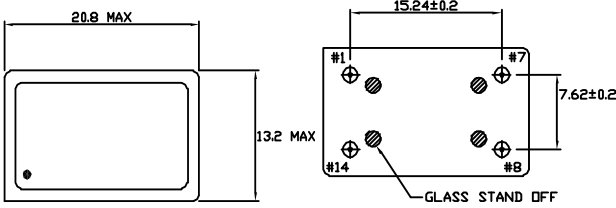
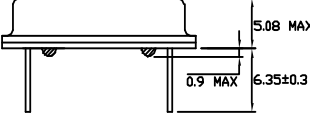
* Jitter Tested at > 1,000,000 samples, exceeding JEDEC std JESD65

Electrical Characteristics:

| Description | Test Conditions | Min | Typ | Max | Unit |
|---|--|-----------------------|-----|-----------------------|------|
| Input Characteristics (Pin 1): | | | | | |
| V _{IL} , Low-Level Input Voltage (To Tri-State or Power Down) | V _{DD} = 5.0 V | - | - | 0.8 | V |
| | V _{DD} = 3.3 V | - | - | 0.2 * V _{DD} | V |
| | V _{DD} = 2.7 V | - | - | 0.2 * V _{DD} | V |
| V _{IH} , High-Level Input Voltage (To Enable Output or Open) | V _{DD} = 5.0 V | 2.0 | - | - | V |
| | V _{DD} = 3.3 V | 0.7 * V _{DD} | - | - | V |
| I _{IL} , Input Low Current | V _{IN} = 0 V | - | - | 10 | μA |
| I _{IH} , Input High Current | V _{IN} = V _{DD} | - | - | 5 | μA |
| Output Characteristics: | | | | | |
| V _{OL} , Low-Level Output Voltage | V _{DD} = 5.0 V, I _{OL} = 16mA | - | - | 0.4 | V |
| | V _{DD} = 3.3 V, I _{OL} = 8mA | - | - | 0.4 | V |
| V _{IHTTL} , High-Level Output Voltage | V _{DD} = 5.0 V, I _{OL} = -16mA | 2.4 | - | - | V |
| V _{IHCMOS} , High-Level Output Voltage | V _{DD} = 5.0 V, I _{OL} = -16mA | V _{DD} -0.4 | - | - | V |
| | V _{DD} = 3.3 V, I _{OL} = -8mA | V _{DD} -0.4 | - | - | V |
| Power Supply Current: (Unloaded) | V _{DD} = 5.0 V, F _O ≤ 133 MHz | - | - | 45 | mA |
| | V _{DD} = 3.3 V, F _O ≤ 100 MHz | - | - | 25 | mA |
| | V _{DD} = 2.7 V, F _O ≤ 66.0 MHz | - | - | 20 | mA |
| Standby Current: | | - | 10 | 50 | μA |
| Tri-State Leakage Current | V _{DD} = 5.0 V | - | 20 | - | μA |
| Output Enable Mode: | Output is Tri-Stated | | | | |
| Power Down Mode: | Output is Tri-Stated | | | | |

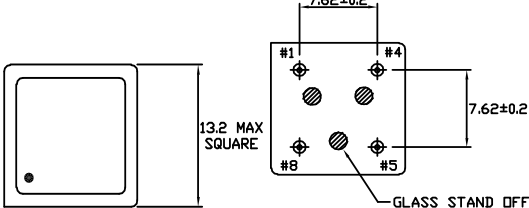
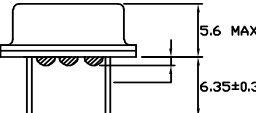
*Note: Bypass V_{DD} to GND with a $0.01\mu\text{F}$ capacitor

Style 1 Full Size 14 Pin Dip

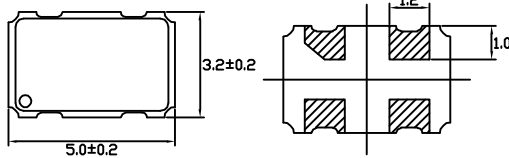
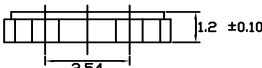
| Pin # | Function |
|-------|----------|
| 1 | Control |
| 7 | GND |
| 8 | Output |
| 14 | V_{DD} |

Style 4 Half Size 8 Pin Dip

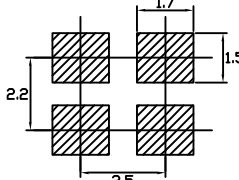



| Pin # | Function |
|-------|----------|
| 1 | Control |
| 4 | GND |
| 5 | Output |
| 8 | V_{DD} |

Style 5 3.2x5 Ceramic SMD

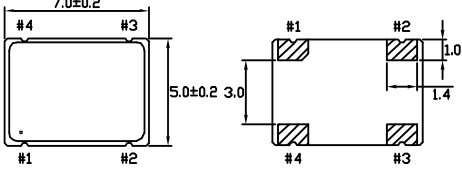
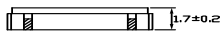



| Pin # | Function |
|-------|----------|
| 1 | Control |
| 2 | GND |
| 3 | Output |
| 4 | V_{DD} |

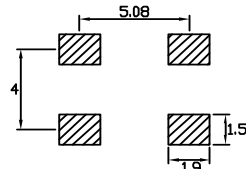


Recommended Solder Pad Layout

Style 7 5x7 Ceramic SMD

| Pin # | Function |
|-------|----------|
| 1 | Control |
| 2 | GND |
| 3 | Output |
| 4 | V_{DD} |



Recommended Solder Pad Layout

*Note: Bypass V_{DD} to GND with a 0.01 μ F capacitor

